Peak gate current (t_p=20εs , T_j=125)	I_{GM}	10	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	25	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33q	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j=125 R_L =3.3kq	- -	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	-	MAX.	80	mA
				120	
I_H	I_T =1A		MAX.	70	mA
dV/dt	V_D=1070V Gate Open T_j=125		MIN.	1500	V/εs
(dI/dt)c	(dV/dt)c=20V/εs T_j=125		MIN.	28	A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	12	εs
t_{off}				80	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =120A t_p=380εs	T_j=25	1.9	V
V_{TO}	Threshold voltage	T_j=125	0.71	V
R_D	Dynamic resistance	T_j=125	23	mq
I_{DRM}	V_D=$V_{DRM}$$V_R$ =V_{RRM}	T_j=25	20	εA
I_{RRM}		T_j=125	12	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	0.27	/W
$R_{th(j-a)}$	junction to ambient (AC)	45	/W

J ST 80 IS -1600 BW

JieJie Microelectronics Co., Ltd.

Triacs

$I_{T(RMS)}$:80A

IS:ITO-247(Ins)

1600:V_{DRM} /V_{RRM} ≥ 1600V

BW:I_{GT1-3} ≤ 50mA

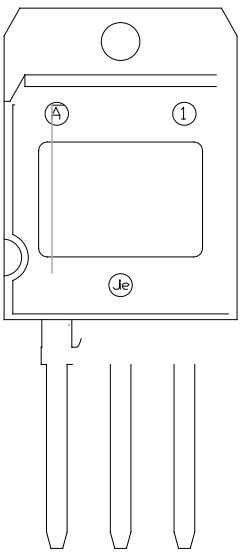


FIG.1: Maximum power dissipation versus RMS on-state current

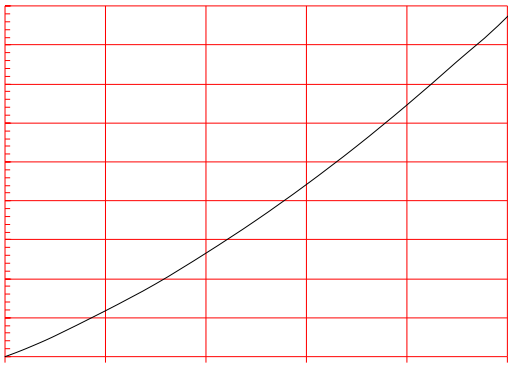


FIG.2: RMS on-state current versus case temperature

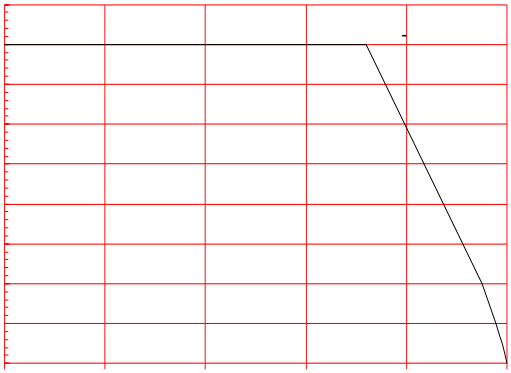
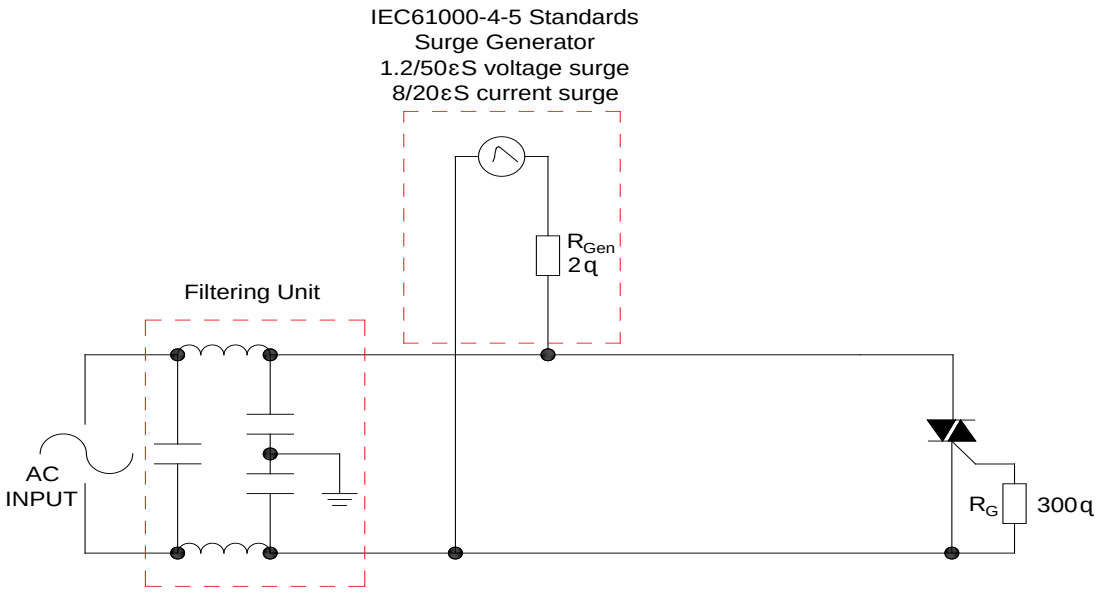


FIG.3: Surge peak on-state current versus number of cycles



FIG.4: On-state characteristic

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie

Order code	Voltage V_{DRM}/V_{RRM}(V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		H- I- J			
JST80IS-1600BW	1600	50	ITO-247		



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJiith S10(d r)10(f)6/6(g)tep cbie, apes es